

1.5MHz Zero-Drift CMOS Rail-to-Rail IO Opamp with RF Filter

Features

- Single-Supply Operation from +2.1V ~ +5.5V
- Rail-to-Rail Input / Output
- Gain-Bandwidth Product: 1.5MHz (Typ. @25°C)
- Low Input Bias Current: 20pA (Typ. @25°C)
- Low Offset Voltage: 5uV (Max. @25°C)
- Quiescent Current: 320µA per Amplifier (Typ.)
- Operating Temperature: -40°C ~ +125°C
- Zero Drift: 0.05µV/°C (Max.)
- Embedded RF Anti-EMI Filter
- Small Package:
HG8551 Available in SOT23-5 and SOP-8 Packages
HG8552 Available in MSOP-8 and SOP-8 Packages

General Description

The HG855X amplifier is single/dual supply, micro-power, zero-drift CMOS operational amplifiers, the amplifiers offer bandwidth of 1.5MHz, rail-to-rail inputs and outputs, and single-supply operation from 2.1V to 5.5V. HG855X uses chopper stabilized technique to provide very low offset voltage (less than 5µV maximum) and near zero drift over temperature. Low quiescent supply current of 320µA per amplifier and very low input bias current of 20pA make the devices an ideal choice for low offset, low power consumption and high impedance applications. The HG855X offers excellent CMRR without the crossover associated with traditional complementary input stages. This design results in superior performance for driving analog-to-digital converters (ADCs) without degradation of differential linearity.

The HG8551 is available in SOT23-5 and SOP8 packages. And the HG8552 is available in MSOP8 and SOP8 packages. The extended temperature range of -40°C to +125°C over all supply voltages offers additional design flexibility.

Applications

- Transducer Application
- Temperature Measurements
- Electronics Scales
- Handheld Test Equipment
- Battery-Powered Instrumentation

Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
HG8551M5/TR	SOT23-5	8551	REEL	3000pcs/reel
HG8551CM/TR	SOP-8L	HG8551C	REEL	2500pcs/reel
HG8552CM/TR	SOP-8L	HG8552C	REEL	2500pcs/reel
HG8552CMM/TR	MSOP-8L	8552C	REEL	3000pcs/reel

Pin Configuration

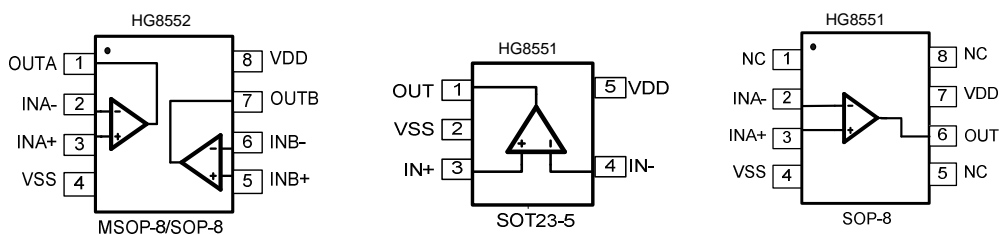


Figure 1. Pin Assignment Diagram

Absolute Maximum Ratings

Condition	Min	Max
Power Supply Voltage (V_{DD} to V_{SS})	-0.5V	+7.5V
Analog Input Voltage ($IN+$ or $IN-$)	$V_{SS}-0.5V$	$V_{DD}+0.5V$
PDB Input Voltage	$V_{SS}-0.5V$	+7V
Operating Temperature Range	-40°C	+125°C
Junction Temperature	+160°C	
Storage Temperature Range	-55°C	+150°C
Lead Temperature (soldering, 10sec)	+260°C	
Package Thermal Resistance ($T_A=+25^\circ\text{C}$)		
SOP-8, θ_{JA}	125°C/W	
MSOP-8, θ_{JA}	216°C/W	
SOT23-5, θ_{JA}	190°C/W	
ESD Susceptibility		
HBM	6KV	
MM	400V	

Note: Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

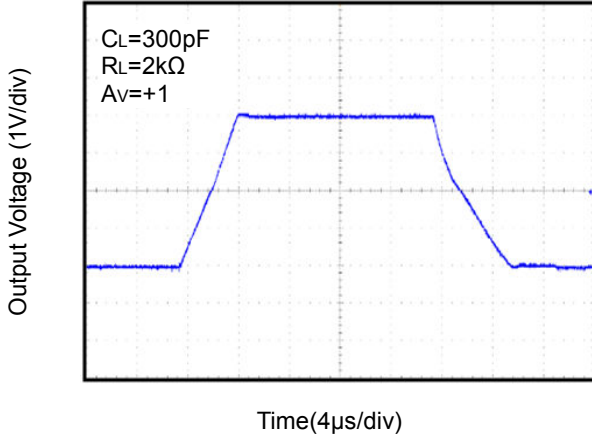
Electrical Characteristics

($V_S = +5V$, $V_{CM} = +2.5V$, $V_O = +2.5V$, $T_A = +25^\circ C$, unless otherwise noted.)

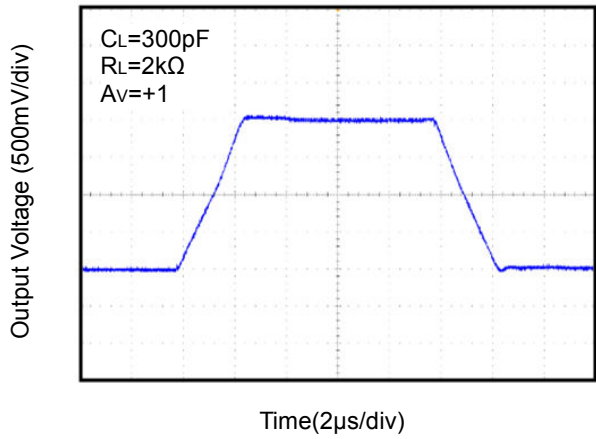
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
INPUT CHARACTERISTICS					
Input Offset Voltage (V_{OS})			1	5	μV
Input Bias Current (I_B)			20		pA
Input Offset Current (I_{OS})			10		pA
Common-Mode Rejection Ratio (CMRR)	$V_{CM} = 0V$ to $5V$		110		dB
Large Signal Voltage Gain (A_{VO})	$R_L = 10k\Omega$, $V_O = 0.3V$ to $4.7V$		145		dB
Input Offset Voltage Drift ($\Delta V_{OS}/\Delta T$)			50		nV/ $^\circ C$
OUTPUT CHARACTERISTICS					
Output Voltage High (V_{OH})	$R_L = 100k\Omega$ to $-V_S$		4.998		V
	$R_L = 10k\Omega$ to $-V_S$		4.994		V
Output Voltage Low (V_{OL})	$R_L = 100k\Omega$ to $+V_S$		2		mV
	$R_L = 10k\Omega$ to $+V_S$		5		mV
Short Circuit Limit (I_{SC})	$R_L = 10\Omega$ to $-V_S$		43		mA
Output Current (I_O)			30		mA
POWER SUPPLY					
Power Supply Rejection Ratio (PSRR)	$V_S = 2.5V$ to $5.5V$		115		dB
Quiescent Current (I_Q)	$V_O = 0V$, $R_L = 0\Omega$		320		μA
DYNAMIC PERFORMANCE					
Gain-Bandwidth Product (GBP)	$G = +100$		1.5		MHz
Slew Rate (SR)	$R_L = 10k\Omega$		0.84		V/ μs
Overload Recovery Time			0.10		ms
NOISE PERFORMANCE					
Voltage Noise (e_n p-p)	0Hz to 10Hz		0.81		μV_{P-P}
Voltage Noise Density (e_n)	$f = 1kHz$		49		nV/ \sqrt{Hz}

Typical Performance characteristics

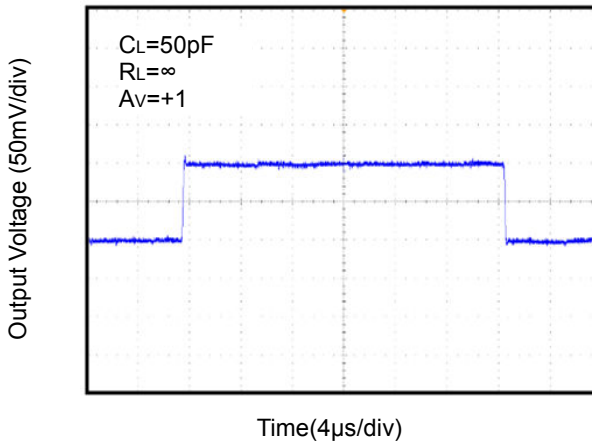
Large Signal Transient Response at +5V



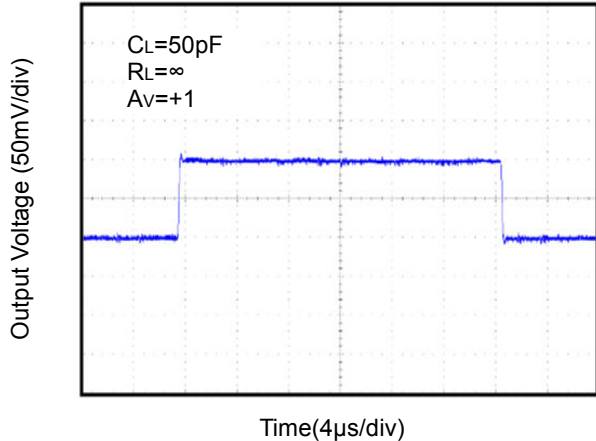
Large Signal Transient Response at +2.5V



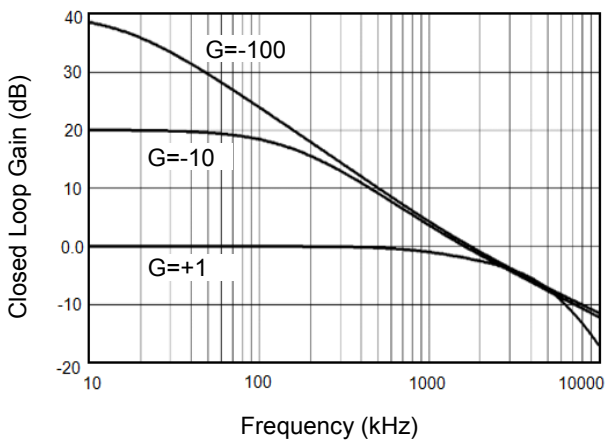
Small Signal Transient Response at +5V



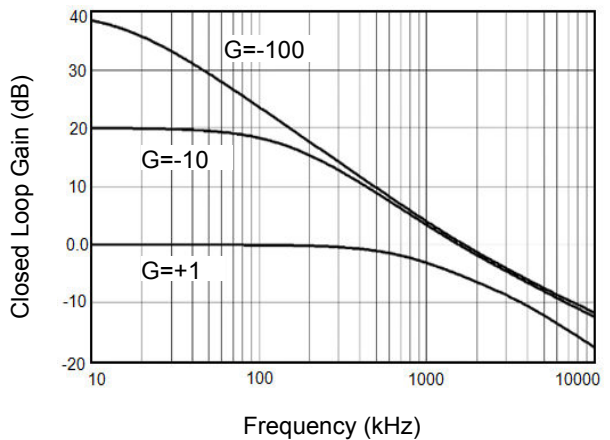
Small Signal Transient Response at +2.5V



Closed Loop Gain vs. Frequency at +5V

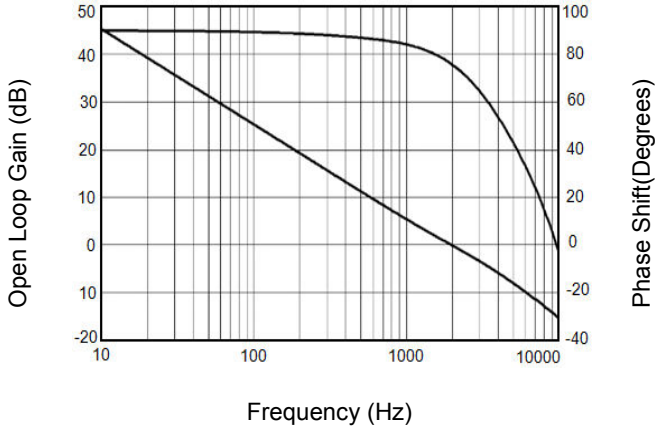


Closed Loop Gain vs. Frequency at +2.5V

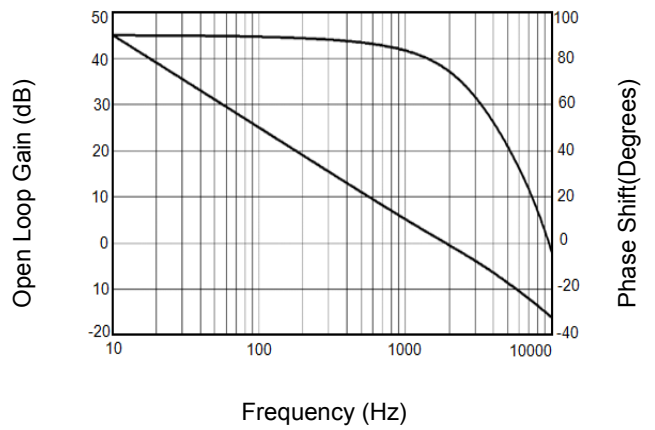


Typical Performance characteristics

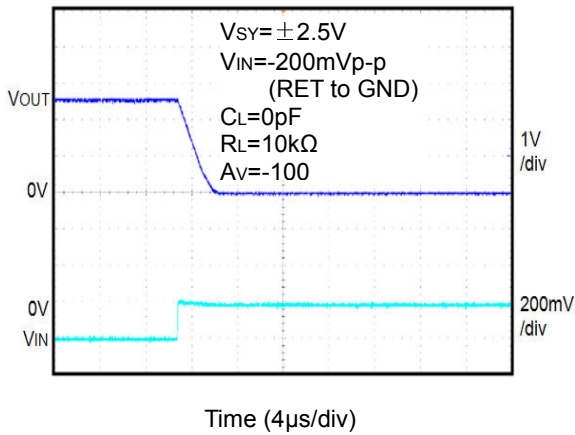
Open Loop Gain, Phase Shift vs. Frequency at +5V



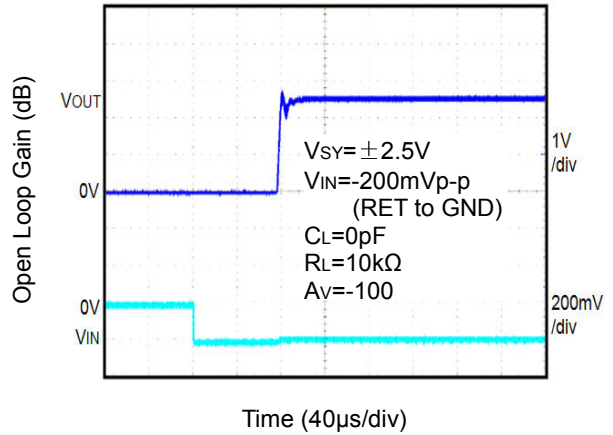
Open Loop Gain, Phase Shift vs. Frequency at +2.5V



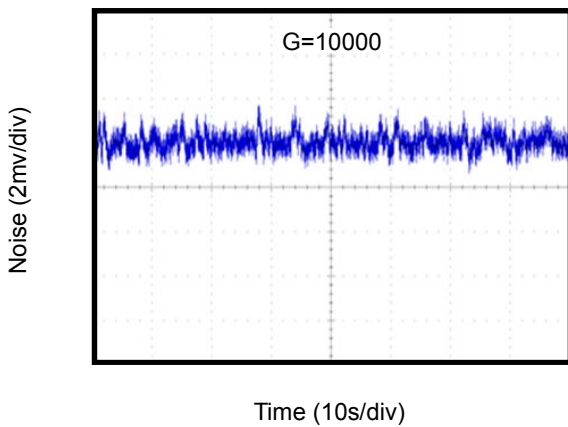
Positive Overvoltage Recovery



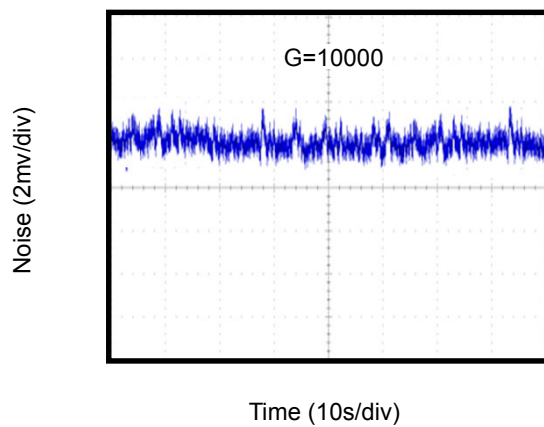
Negative Overvoltage Recovery



0.1Hz to 10Hz Noise at +5V



0.1Hz to 10Hz Noise at +2.5V



Application Note

Size

HG855X series op amps are unity-gain stable and suitable for a wide range of general-purpose applications. The small footprints of the HG855X series packages save space on printed circuit boards and enable the design of smaller electronic products.

Power Supply Bypassing and Board Layout

HG855X series operates from a single 2.1V to 5.5V supply or dual $\pm 1.05\text{V}$ to $\pm 2.75\text{V}$ supplies. For best performance, a $0.1\mu\text{F}$ ceramic capacitor should be placed close to the V_{DD} pin in single supply operation. For dual supply operation, both V_{DD} and V_{SS} supplies should be bypassed to ground with separate $0.1\mu\text{F}$ ceramic capacitors.

Low Supply Current

The low supply current (typical $320\mu\text{A}$ per channel) of HG855X series will help to maximize battery life. They are ideal for battery powered systems.

Operating Voltage

HG855X series operate under wide input supply voltage (2.1V to 5.5V). In addition, all temperature specifications apply from -40°C to $+125^\circ\text{C}$. Most behavior remains unchanged throughout the full operating voltage range. These guarantees ensure operation throughout the single Li-Ion battery lifetime.

Rail-to-Rail Input

The input common-mode range of HG855X series extends 100mV beyond the supply rails ($V_{\text{SS}}-0.1\text{V}$ to $V_{\text{DD}}+0.1\text{V}$). This is achieved by using complementary input stage. For normal operation, inputs should be limited to this range.

Rail-to-Rail Output

Rail-to-Rail output swing provides maximum possible dynamic range at the output. This is particularly important when operating in low supply voltages. The output voltage of HG855X series can typically swing to less than 5mV from supply rail in light resistive loads ($>100\text{k}\Omega$), and 60mV of supply rail in moderate resistive loads ($10\text{k}\Omega$).

Capacitive Load Tolerance

The HG855x family is optimized for bandwidth and speed, not for driving capacitive loads. Output capacitance will create a pole in the amplifier's feedback path, leading to excessive peaking and potential oscillation. If dealing with load capacitance is a requirement of the application, the two strategies to consider are (1) using a small resistor in series with the amplifier's output and the load capacitance and (2) reducing the bandwidth of the amplifier's feedback loop by increasing the overall noise gain. Figure 2. shows a unity gain follower using the series resistor strategy. The resistor isolates the output from the capacitance and, more importantly, creates a zero in the feedback path that compensates for the pole created by the output capacitance.

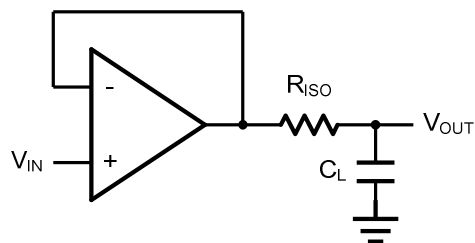


Figure 2. Indirectly Driving a Capacitive Load Using Isolation Resistor

The bigger the R_{ISO} resistor value, the more stable V_{OUT} will be. However, if there is a resistive load R_{L} in parallel with the capacitive load, a voltage divider (proportional to $R_{\text{ISO}}/R_{\text{L}}$) is formed, this will result in a gain error.

The circuit in Figure 3 is an improvement to the one in Figure 2. R_{F} provides the DC accuracy by feed-forward the V_{IN} to R_{L} . C_{F}

and R_{ISO} serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving the phase margin in the overall feedback loop. Capacitive drive can be increased by increasing the value of C_F . This in turn will slow down the pulse response.

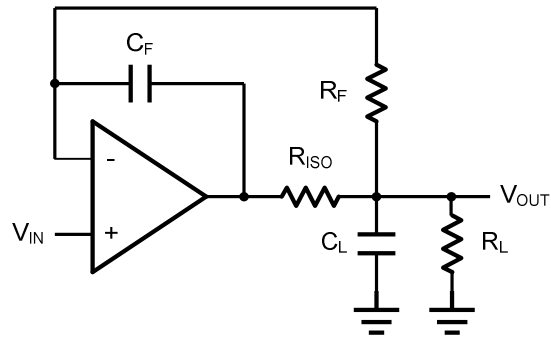


Figure 3. Indirectly Driving a Capacitive Load with DC Accuracy

Typical Application Circuits

Differential amplifier

The differential amplifier allows the subtraction of two input voltages or cancellation of a signal common the two inputs. It is useful as a computational amplifier in making a differential to single-end conversion or in rejecting a common mode signal. Figure 4. shown the differential amplifier using HG855X.

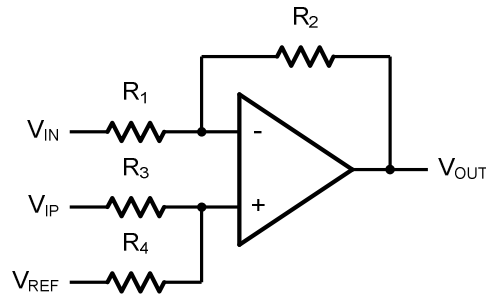


Figure 4. Differential Amplifier

$$V_{OUT} = \left(\frac{R_1+R_2}{R_3+R_4}\right) \frac{R_4}{R_1} V_{IN} - \frac{R_2}{R_1} V_{IP} + \left(\frac{R_1+R_2}{R_3+R_4}\right) \frac{R_3}{R_1} V_{REF}$$

If the resistor ratios are equal (i.e. $R_1=R_3$ and $R_2=R_4$), then

$$V_{OUT} = \frac{R_2}{R_1} (V_{IP} - V_{IN}) + V_{REF}$$

Low Pass Active Filter

The low pass active filter is shown in Figure 5. The DC gain is defined by $-R_2/R_1$. The filter has a -20dB/decade roll-off after its corner frequency $f_c=1/(2\pi R_3 C_1)$.

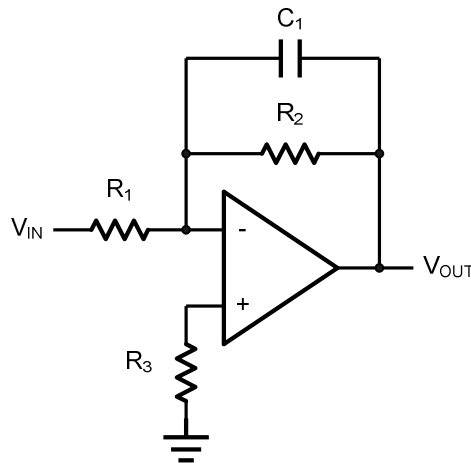


Figure 5. Low Pass Active Filter

Instrumentation Amplifier

The triple HG855X can be used to build a three-op-amp instrumentation amplifier as shown in Figure 6. The amplifier in Figure 6 is a high input impedance differential amplifier with gain of R_2/R_1 . The two differential voltage followers assure the high input impedance of the amplifier.

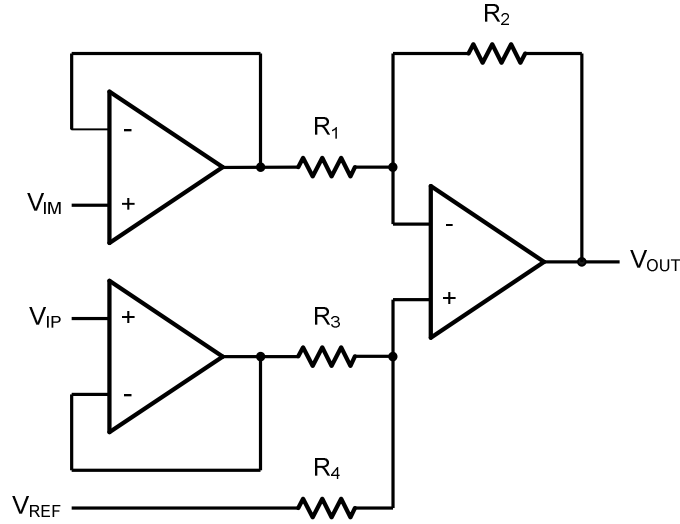
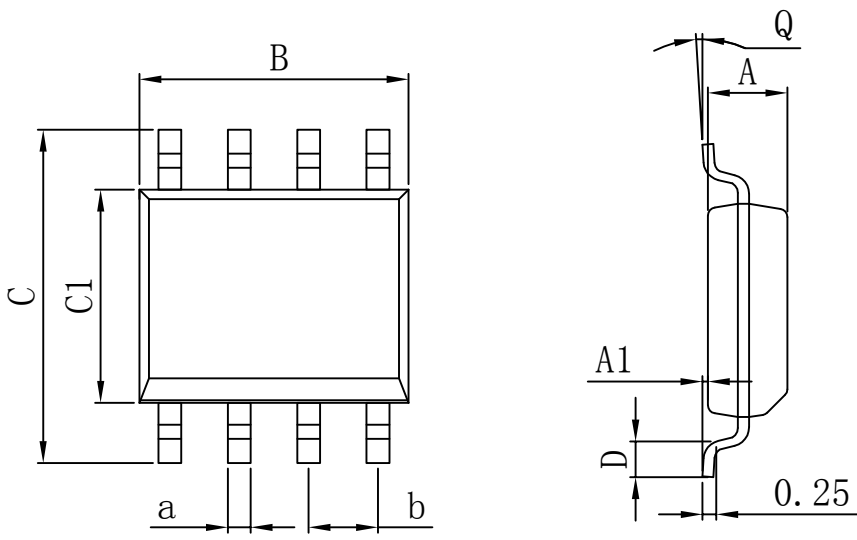


Figure 6. Instrument Amplifier

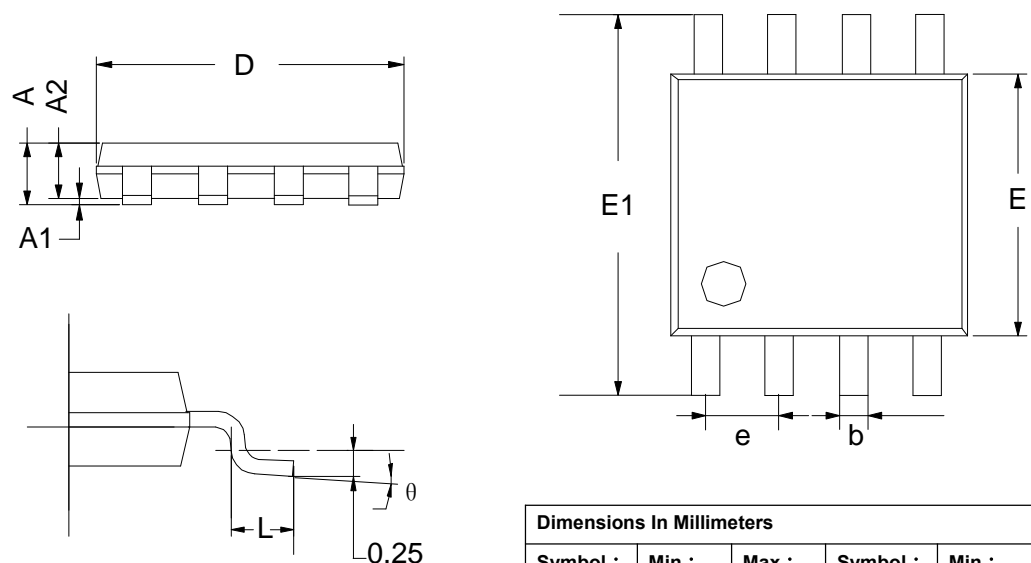
Package Information

SOP8



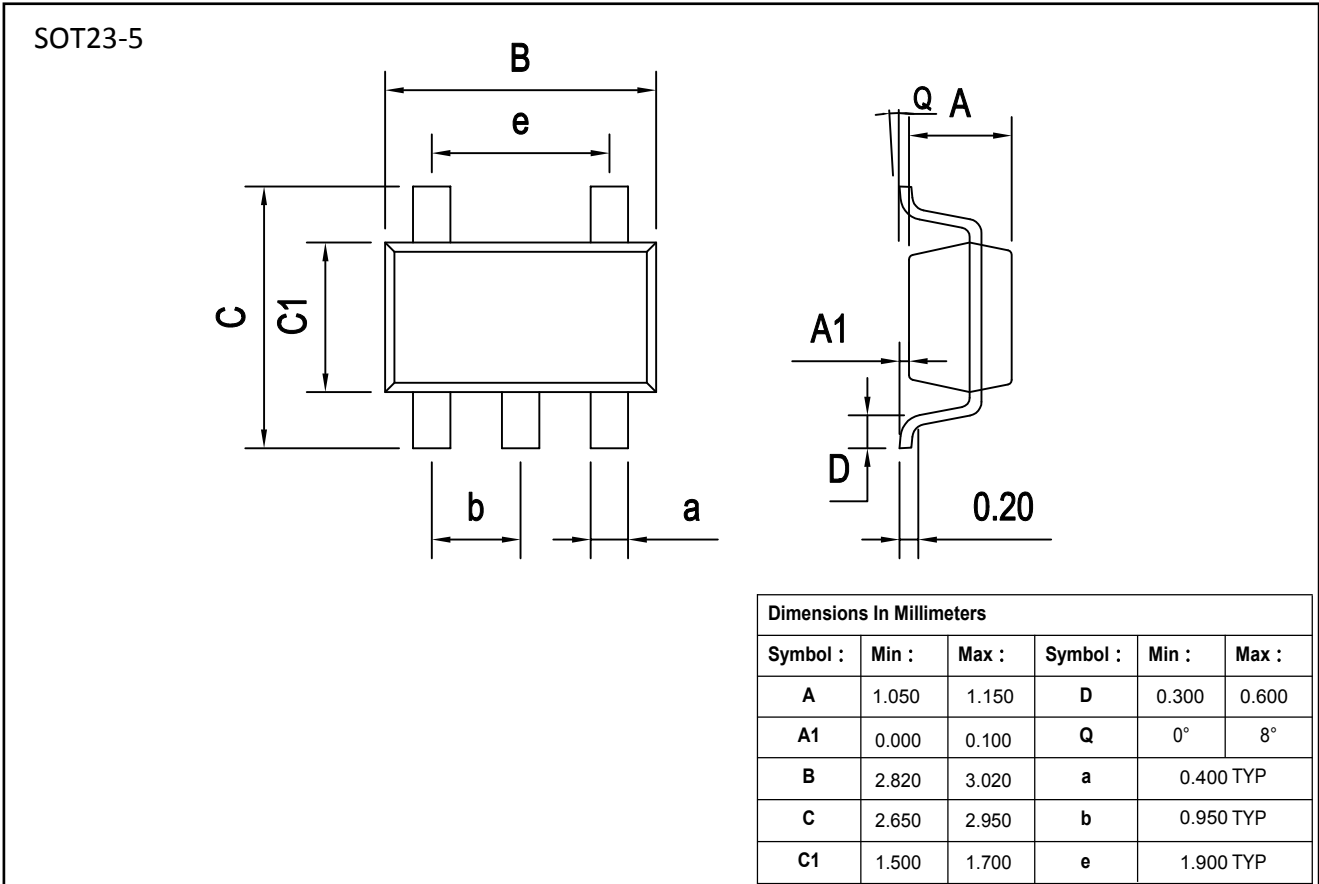
Dimensions In Millimeters					
Symbol :	Min :	Max :	Symbol :	Min :	Max :
A	1.225	1.570	D	0.400	0.950
A1	0.100	0.250	Q	0°	8°
B	4.800	5.100	a	0.420 TYP	
C	5.800	6.250	b	1.270 TYP	
C1	3.800	4.000			

MSOP8



Dimensions In Millimeters					
Symbol :	Min :	Max :	Symbol :	Min :	Max :
A	0.800	1.200	E1	4.700	5.100
A1	0	0.200	L	0.410	0.650
A2	0.760	0.970	θ	0°	6°
D	2.900	3.100	b	0.300 TYP	
E	2.900	3.100	e	0.650 TYP	

Package Information



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